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## **KSA954**

## **Audio Frequency Amplifier**



### 1. Emitter 2. Collector 3. Base

### **PNP Epitaxial Silicon Transistor**

### Absolute Maximum Ratings T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>CBO</sub>	Collector-Base Voltage	-80	110V.
V <sub>CEO</sub>	Collector-Emitter Voltage	-80	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	11.V
Ic	Collector Current (DC)	-300	mA
I <sub>CP</sub>	* Collector Current (Pulse)	-500	mA
P <sub>C</sub>	Collector Dissipation	600	mW
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

<sup>\*</sup> PW≤10ms, Duty Cycle≤50% Pulsed

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = -80V, I_{E} = 0$	Mo.	1.41	-100	nA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{BE}$ = -5V, $I_{C}$ =0	I.Co.	WT	-100	nA
h <sub>FE1</sub> h <sub>FE2</sub>	* DC Current Gain	$V_{CE}$ = -1V, $I_{C}$ = -50mA $V_{CE}$ = -2V, $I_{C}$ = -300mA	90 30	200 80	400	WW
V <sub>BE</sub> (on)	* Base Emitter On Voltage	$V_{CE}$ = -6V, $I_{C}$ = -10mA	-600	-660	700	mV
V <sub>BE</sub> (sat)	* Base Emitter Saturation Voltage	I <sub>C</sub> = -300mA, I <sub>B</sub> = -30mA	JO -	-0.85	-1.2	V
V <sub>CE</sub> (sat)	Collector -Emitter Saturation Voltage	I <sub>C</sub> = -300mA, I <sub>B</sub> = -30mA	00 A .	-0.15	-0.6	V
C <sub>ob</sub>	Output Capacitance	$V_{CB}$ = -6V, $I_{E}$ =0, $f$ =1MHz	onV.	13	25	pF⊸
f <sub>T</sub>	Current Gain-Bandwidth Product	V <sub>CE</sub> = -6V, I <sub>C</sub> = -10mA	50	100	1	MHz
	≤350μs, Duty Cycle≤2% assification	M.IM WW.	M.100	N.CO	V.T.	
Cla	ssification	Y			G	

### h<sub>FF1</sub> Classification

Classification	100	Υ	G	
h <sub>FE1</sub>	90 ~ 180	135 ~ 270	200 ~ 400	
''FE1	90 ~ 100	155 ~ 270	200 ~ 400	

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## **Typical Characteristics**

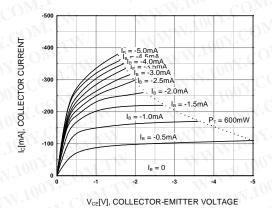


Figure 1. Static Characterstic

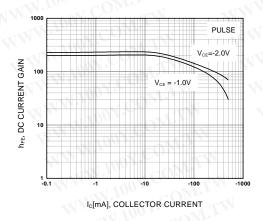


Figure 3. DC current Gain

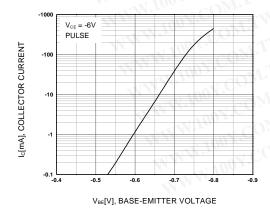


Figure 5. Base-Emitter On Voltage

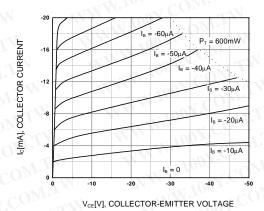


Figure 2. Static Characteristic

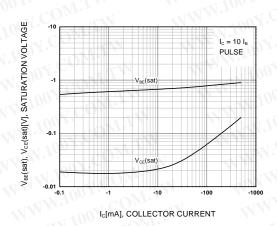
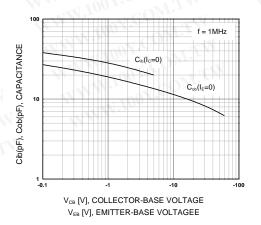


Figure 4. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage



**Figure 6. Input Output Capacitance** 

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## WWW.100Y.COM.TW Typical Characteristics (Continued)

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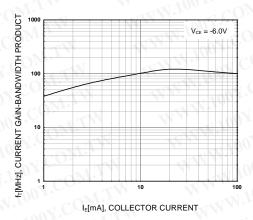


Figure 7. Gain Bandwidth Product

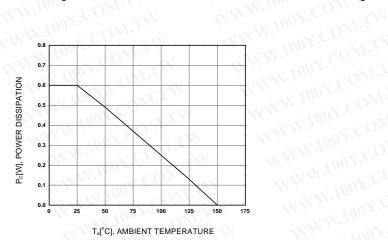


Figure 9. Power Derating WWW.100Y.C WWW.100Y.COM.TW

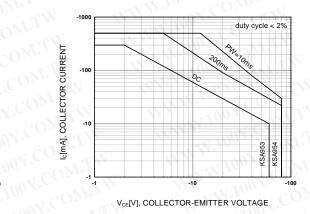


Figure 8. Safe Operating Area WWW.100Y.COM

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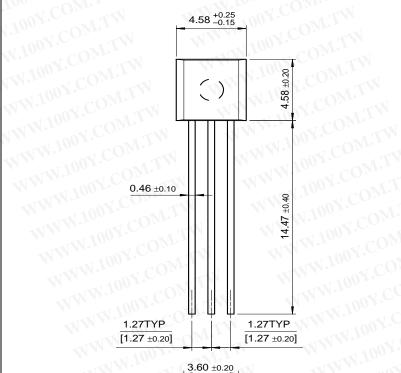
# WWW.100Y.COM.TW **Package Demensions** WWW.100Y.COM.TW

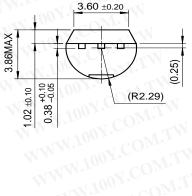
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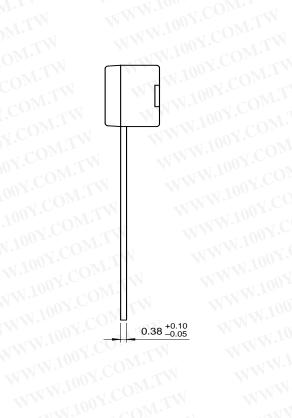
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**Dimensions in Millimeters** 

WWW.10

SuperSOT™-8

SyncFET™

TinyLogic™

UHC™

VCX™

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